

Silicon PNP Power Transistors

2SA1383

DESCRIPTION

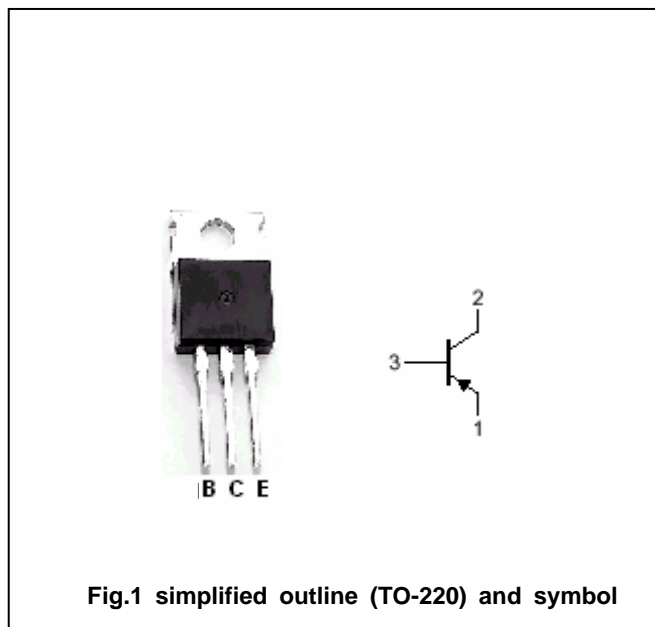
- With TO-220 package
- Complement to type 2SC3514
- High transition frequency

APPLICATIONS

- Designed for use in audio frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-180	V
V_{CEO}	Collector-emitter voltage	Open base	-180	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-0.1	A
P_C	Collector power dissipation	$T_a=25$	1.5	W
		$T_C=25$	10	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA, I _B =0	-180			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-50mA; I _B =-5mA			-0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-50mA; I _B =-5mA			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-180V; I _E =0			-1.0	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-3V; I _C =0			-1.0	μA
h _{FE-1}	DC current gain	I _C =-1mA; V _{CE} =-5V	90			
h _{FE-2}	DC current gain	I _C =-10mA; V _{CE} =-5V	100		320	
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V; f=1MHz		4.5		pF
f _T	Transition frequency	I _C =-20mA; V _{CE} =-10V		180		MHz

◆ h_{FE-2} Classifications

Q	P
100-200	160-320

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PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)